

L Number	Hits	Search Text	DB	Time stamp
1	245	three near3 dimensional near3 growth and sb	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/23 13:00
2	14	three near3 dimensional near3 growth same sb	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/23 12:45
3	26	three near3 dimensional near3 growth same (quantum near3 well\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/23 12:46
4	8	(three near3 dimensional near3 growth same (quantum near3 well\$1)) and sb	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/23 12:55
5	16	(qw or (quantum near3 well\$1)) same gainassb	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/23 13:01
6	0	three near3 dimensional near3 growth and ((qw or (quantum near3 well\$1)) same gainassb)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/23 13:00
7	2	(qw or (quantum near3 well\$1)) and gainassb and three near3 dimensional near3 growth	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/23 13:05
13	2	(qw or (quantum near3 well\$1)) and gainassb and ((three near3 dimensional near3 growth) or islanding) and (sb or surfactant)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/23 13:07
14	2	gainassb and ((three near3 dimensional near3 growth) or islanding) and (sb or surfactant)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/23 13:26
15	48	(qw or (quantum near3 well\$1)) and ((three near3 dimensional near3 growth) or islanding) and (sb or surfactant)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/23 13:08
16	8	((qw or (quantum near3 well\$1)) and ((three near3 dimensional near3 growth) or islanding) and (sb or surfactant)) and 372/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/23 13:08
17	83	gainassb	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/23 13:26
18	2	gainassb and ((three near3 dimensional near3 growth) or islanding)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/23 13:29
19	7	gainassb and 372/43.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/23 13:27
20	11	372/43.ccls. and ((three near3 dimensional near3 growth) or islanding)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/23 13:33
21	0	372/43.ccls. and suppress\$3 near3 ((three near3 dimensional near3 growth) or islanding)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/23 13:34

22	2	372/45.ccls. and suppress\$3 near3 ((three near3 dimensional near3 growth) or islanding)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/23 13:35
23	4	372/\$.ccls. and suppress\$3 near3 ((three near3 dimensional near3 growth) or islanding)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/23 13:56
24	2	(("6330263") or ("6566688")).PN.	USPAT; US-PGPUB	2004/05/23 13:57

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1	245	three near3 dimensional near3 growth and sb	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/23 13:00
2	14	three near3 dimensional near3 growth same sb	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/23 12:45
3	26	three near3 dimensional near3 growth same (quantum near3 well\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/23 12:46
4	8	(three near3 dimensional near3 growth same (quantum near3 well\$1)) and sb	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/23 12:55
5	16	(qw or (quantum near3 well\$1)) same gainassb	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/23 13:01
6	0	three near3 dimensional near3 growth and ((qw or (quantum near3 well\$1)) same gainassb)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/23 13:00
7	2	(qw or (quantum near3 well\$1)) and gainassb and three near3 dimensional near3 growth	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/23 13:05
13	2	(qw or (quantum near3 well\$1)) and gainassb and ((three near3 dimensional near3 growth) or islanding) and (sb or surfactant)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/23 13:07
14	2	gainassb and ((three near3 dimensional near3 growth) or islanding) and (sb or surfactant)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/23 13:26
15	48	(qw or (quantum near3 well\$1)) and ((three near3 dimensional near3 growth) or islanding) and (sb or surfactant)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/23 13:08
16	8	((qw or (quantum near3 well\$1)) and ((three near3 dimensional near3 growth) or islanding) and (sb or surfactant)) and 372/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/23 13:08
17	83	gainassb	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/23 13:26
18	2	gainassb and ((three near3 dimensional near3 growth) or islanding)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/23 13:29
19	7	gainassb and 372/43.cccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/23 13:27
20	11	372/43.cccls. and ((three near3 dimensional near3 growth) or islanding)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/23 13:33
21	0	372/43.cccls. and suppress\$3 near3 ((three near3 dimensional near3 growth) or islanding)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/23 13:34

22	2	372/45.ccls. and suppress\$3 near3 ((three near3 dimensional near3 growth) or islanding)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/23 13:35
23	4	372/\$.ccls. and suppress\$3 near3 ((three near3 dimensional near3 growth) or islanding)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/23 13:56
24	2	(("6330263") or ("6566688")).PN.	USPAT; US-PGPUB	2004/05/23 13:57
-	9	quantum near3 well\$1 and (gainassb or gainasnsb) and gaas and (vcsel or (edge near3 emitting))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/23 12:26
-	699	quantum near3 well\$1 and nitride and (substrate near3 gaas)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/10/30 14:16
-	2	(quantum near3 well\$1 and nitride and (substrate near3 gaas)) and barrier near3 ganas	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/10/30 14:16
-	10	quantum near3 well\$1 and (substrate near3 gaas) and gainassb	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/10/30 14:44
-	1	quantum near3 well\$1 and (substrate near3 gaas) and gainasnsb and barrier near3 ganas	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/10/30 14:45
-	1	gainasnsb and ganas	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/10/30 14:46
-	7	gainasnsb	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/10/30 14:48
-	10	vcsel and nitrogen and antimony and wavelength near3 increas\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/10/30 14:50
-	24	vcsel and nitrogen and (antimony or sb) and wavelength near3 increas\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/10/30 15:46
-	454	quantum near3 well\$1 and (nitrogen or nitride) and (antimony or sb)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/10/30 15:55
-	17	(quantum near3 well\$1 and (nitrogen or nitride) and (antimony or sb)) and barrier near3 (ganas or gaasn or asgan or asnga or ngaas or nasga)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/10/30 15:49
-	17	(quantum near3 well\$1 and (nitrogen or nitride) and (antimony or sb)) and barrier\$1 near3 (ganas or gaasn or asgan or asnga or ngaas or nasga)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/10/30 15:49
-	18	quantum near3 well\$1 and barrier\$1 near3 (ganas or gaasn or asgan or asnga or ngaas or nasga) and (antimony or sb)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/10/30 16:06
-	18	barrier\$1 near3 (ganas or gaasn or asgan or asnga or ngaas or nasga) and (antimony or sb)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/10/30 16:21

	7	(gainasn or ingaasn) and barrier near3 (ganas or gaasn or asgan or asnga or ngaas or nasga) and (antimony or sb)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/10/30 16:23
	29	(gainasn or ingaasn) and (ganas or gaasn or asgan or asnga or ngaas or nasga) and (antimony or sb)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/10/30 16:27
	30	(gainasn or ingaasn or gainasnb or ingaasnsb) and (ganas or gaasn or asgan or asnga or ngaas or nasga) and (antimony or sb)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/10/30 16:28
	8	(gainasnsb or ingaasnsb) and (ganas or gaasn or asgan or asnga or ngaas or nasga)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/10/30 16:32
	143	nitride near3 semiconductor and quantum near3 well\$1 and barrier\$1 and (antimony or sb)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/10/30 17:22
	6	(nitride near3 semiconductor and quantum near3 well\$1 and barrier\$1 and (antimony or sb)) and increas\$3 near3 wavelength	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/10/30 17:24
	4	(nitride near3 semiconductor and quantum near3 well\$1 and barrier\$1 and (antimony or sb)) and vcsel	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/10/30 17:26
	29	(nitride near3 semiconductor and quantum near3 well\$1 and barrier\$1 and (antimony or sb)) and (substrate near3 (gaas or asga))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/10/30 17:26
	31	(ingaassb or gainassb) and nitride	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/10/31 11:08
	0	Indium near3 Gallium near3 Arsenic near3 Antimonide near3 nitrogen	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/10/31 10:54
	20	Antimonide near3 nitrogen	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/10/31 10:58
	32	Antimonide and nitrogen and gallium and indium and arsenic and semiconductor near3 laser	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/10/31 10:59
	9	(ingaasnsb or gainasnsb)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/10/31 11:08